



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON) max}	Package	I _{D max} T _A = +25°C
-20V	60mΩ @ V _{GS} = -4.5V	SOT-23	-4.0A
-20V	90mΩ @ V _{GS} = -2.5V	501-23	-3.3A

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Description and Applications

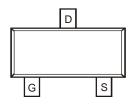
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Mechanical Data

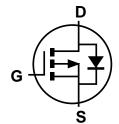
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 (3)
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Lead-Frame).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)







Top View Pin Configuration



Equivalent Circuit

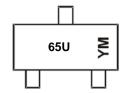
Ordering Information (Note 4)

Ī	Part Number	Case	Packaging
	DMP2065U-7	SOT23	3000/Tape & Reel
ı	DMP2065U-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



65U = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	202	0	2021		2022	20	23	2024		2025	2	2026
Code	Н		ı		J	ı	`	L		М		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ T_A = +25°C unless otherwise specified.)

Characterist	ic	Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 6) V _{GS} = -4.5V	Steady $T_A = +25$ °C State $T_A = +70$ °C	I _D	-4.0 -3.0	Α
Pulsed Drain Current (Pulse width ≤10µS,	Duty Cycle ≤1%)	I _{DM}	-15	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	138	°C/W
Total Power Dissipation (Note 6)		P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	83	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

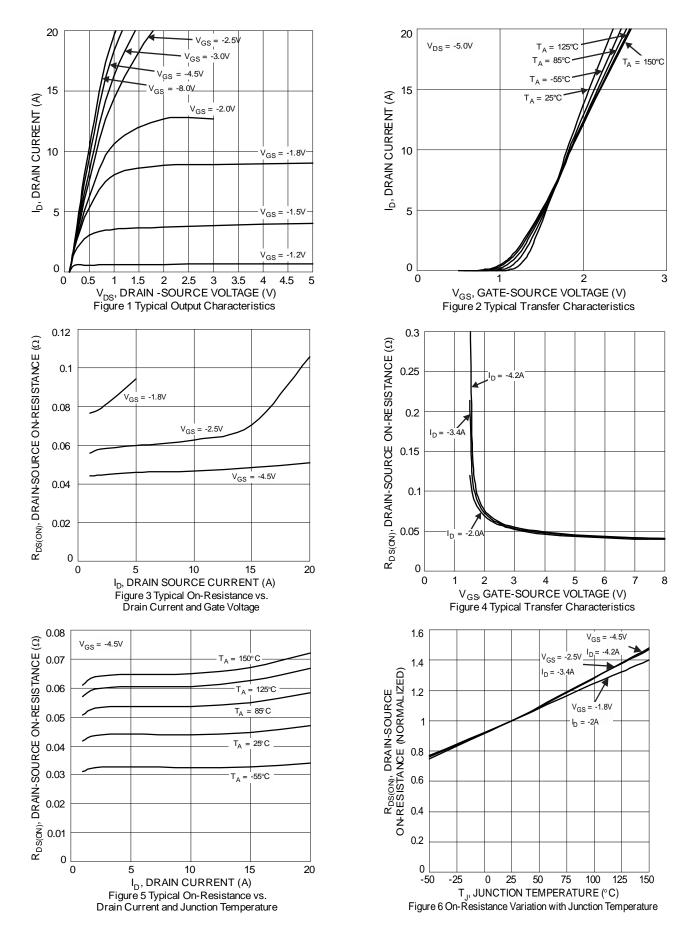
Electrical Characteristics (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			- 76			
Drain-Source Breakdown Voltage	BV_{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25$ °C	I _{DSS}	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±50	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			41	60		$V_{GS} = -4.5V$, $I_{D} = -4.2A$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	53	90	mΩ	$V_{GS} = -2.5V$, $I_D = -3.4A$
			72	113		$V_{GS} = -1.8V$, $I_D = -2.0A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.1	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	808		pF	V 45V V 6V
Output Capacitance	Coss	_	85		pF	$V_{DS} = -15V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	77		pF	1 = 1.0WH IZ
Gate Resistance	R _G	_	15.2		Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$
Total Gate Charge	Q_g	_	10.2		nC	
Gate-Source Charge	Q_{gs}	_	1.3	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -4V$, $I_{D} = -3.5A$
Gate-Drain Charge	Q_{gd}	_	2.2	_	nC	
Turn-On Delay Time	t _{D(on)}	_	10.8	_	ns	
Turn-On Rise Time	t _r		13.7	_	ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,
Turn-Off Delay Time	t _{D(off)}		79.3	_	ns	$R_L = 4\Omega$, $R_G = 6\Omega$, $I_D = -1A$
Turn-Off Fall Time	t _f		34.7	_	ns	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







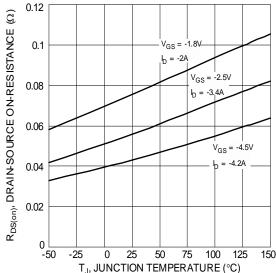
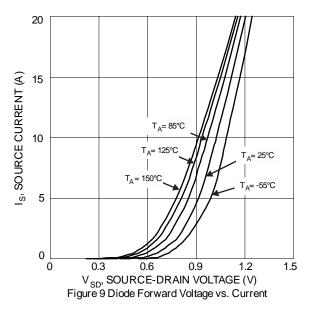
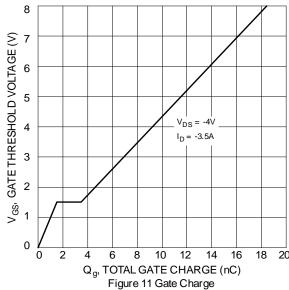


Figure 7 On-Resistance Variation with Junction Temperature





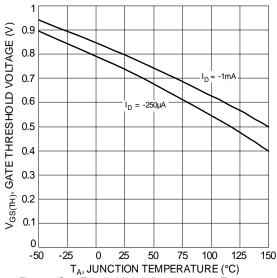
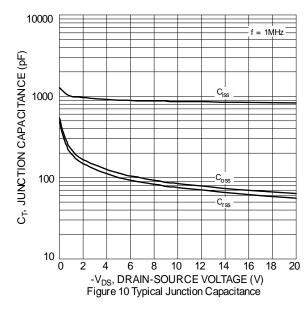
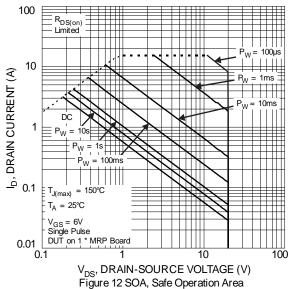
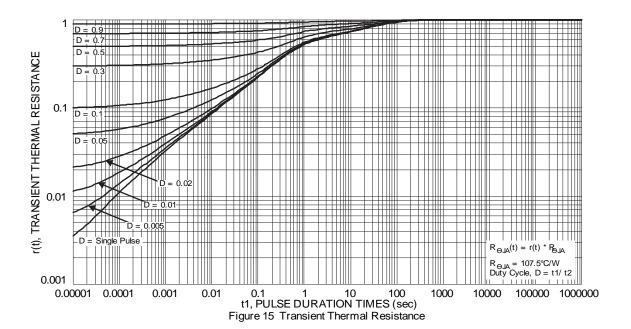


Figure 8 Gate Threshold Variation vs. Junction Temperature







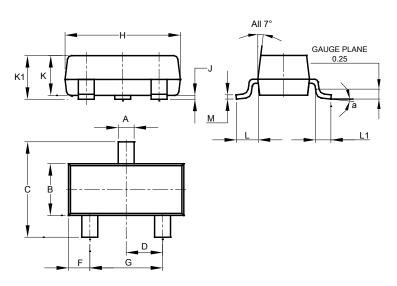




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

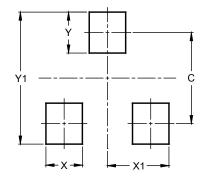


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
V1	2.0			



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